

AN 1989-155239 [21] WPIDS  
DNN N1989-118216 DNC C1989-068848  
TI Clad target sputtering material - includes copper substrate containing zinc,  
indium, manganese, antimony beryllium, calcium, etc..  
DC M13 U11  
PA (TANI) TANAKA KIKINZOKU KOGYO KK  
CYC 1  
PI JP 01096374 A 19890414 (198921)\* 3<--  
ADT JP 01096374 A JP 1987-251174 19871005  
PRAI JP 1987-251174 19871005  
AB JP 01096374 A UPAB: 19930923

A sputtering clad target material is composed of target material clad  
through metal bonding agent to a more than 99.7% purity Cu substrate  
including at least one of Zn, In, Mn, Sb, Be, Ca, Cr, Te, Y, Nb, Mo, Ta  
and Sn 100-3000 weight ppm in total. The substrate contacting a backing  
plate is not pressure-bonded.

1-3/3